

U.S. Department of Commerce, Patent and Trademark				Atty. Docket No.		Application No.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				SNDK.352US0		10/799,060	
				Applicant(s)			
(Use several sheets if necessary)				Filing Date		Group	
JAN 24 2005				March 12, 2004		2818	
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Examiner	Date Considered			08/11/05			
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(Use several sheets if necessary)				Jeffrey Lutze et al.			
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(Form PTO-1449)	Jeffrey W. LUTZE et al.	6740
1 of 2	Filing Date	Art Group
	March 12, 2004	2818

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